

# MSF13N50

## N-Channel 500V MOSFET

### Description

The MSF13N50 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220AB package is universally preferred for all commercial-industrial applications

### Features

- RDS(on) (Typical 0.48 Ω)@VGS=10V
- Gate Charge (Typical 43 nC)
- Improved dv/dt Capability, High Ruggedness
- 100% Avalanche Tested
- Maximum Junction Temperature Range (150°C)
- RoHS compliant package

### Application

- Open Framed Power Supply
- Adapter
- STB

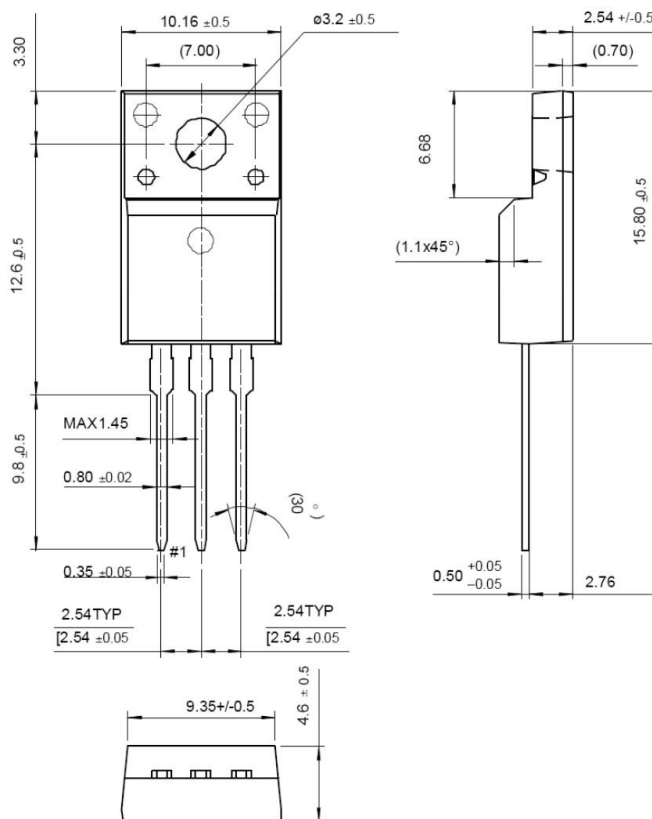
Package type : ITO220-AB

### Packing & Order Information

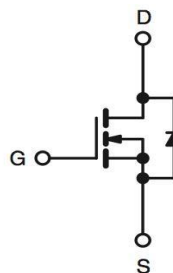
50/Tube ; 1,000/Box



**RoHS**  
COMPLIANT



### Graphic symbol



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain-Source Voltage	500	V
V <sub>GS</sub>	Gate-Source Voltage	±30	V
I <sub>D</sub>	Drain Current -Continuous (TC=25°C)	13	A
	Drain Current -Continuous (TC=100°C)	8	A
I <sub>DM</sub>	Drain Current Pulsed	52	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy	939	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy	19.5	mJ
dV/dt	Peak Diode Recovery dV/dt	4.5	V/ns
P <sub>D</sub>	Power Dissipation (TC = 25 °C)	48	W
	- Derate above 25 °C	0.39	W/°C

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#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

- Drain current limited by maximum junction temperature

#### Thermal characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameter	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	2.5	°C/W
R <sub>θJA</sub>	Junction-to-Ambient	62.5	

#### On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
V <sub>GS</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	--	4.0	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6.5A	--	0.39	0.48	Ω

#### Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0 V, I <sub>D</sub> =250μA	500	--	--	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA, Referenced to 25°C	--	0.5	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =500V, V <sub>GS</sub> =0 V V <sub>DS</sub> =400V, T <sub>C</sub> =125°C	--	--	10 100	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> =30V, V <sub>DS</sub> =0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> =-30V, V <sub>DS</sub> =0 V	--	--	-100	nA

#### Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	--	1600	--	pF
C <sub>OSS</sub>	Output Capacitance		--	180	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	20	--	pF

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Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Time	$V_{DS}=250\text{ V}, I_D=6.5\text{ A},$ $R_G=25\Omega$	--	30	--	ns
$t_r$	Turn-On Time		--	120	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	120	--	ns
$t_f$	Turn-Off Fall Time		--	100	--	ns
$Q_g$	Total Gate Charge	$V_{DS}=400\text{ V}, I_D=6.5\text{ A},$ $V_{GS}=10\text{ V}$	--	43	--	nC
$Q_{gs}$	Gate-Source Charge		--	8	--	nC
$Q_{gd}$	Gate-Drain Charge		--	19	--	nC

Source-Drain Diode Maximum Ratings and Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$I_S$	Continuous Source-Drain Diode Forward Current		--	--	13.0	A
$I_{SM}$	ISM Pulsed Source-Drain Diode Forward Current		--	--	52.0	
$V_{SD}$	Source-Drain Diode Forward Voltage	$I_S=13\text{ A}, V_{GS}=0\text{ V}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$I_S=13\text{ A}, V_{GS}=0\text{ V}$ $diF/dt=100\text{ A}/\mu\text{s}$	--	400	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	4.5	--	$\mu\text{C}$

Notes ;

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L=5.0\text{ mH}, I_{AS}=13\text{ A}, V_{DD}=50\text{ V}, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
3.  $I_{SD} \leq 13\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$
4. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature

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#### ■ Characteristics Curve

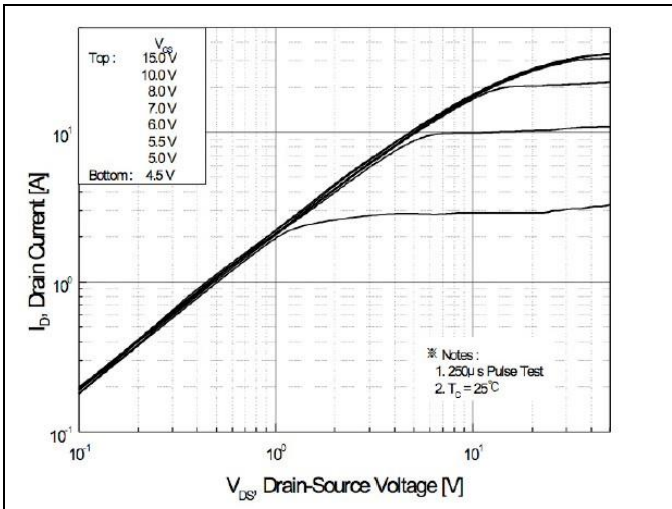


FIG. 1-ON REGION CHARACTERISTICS

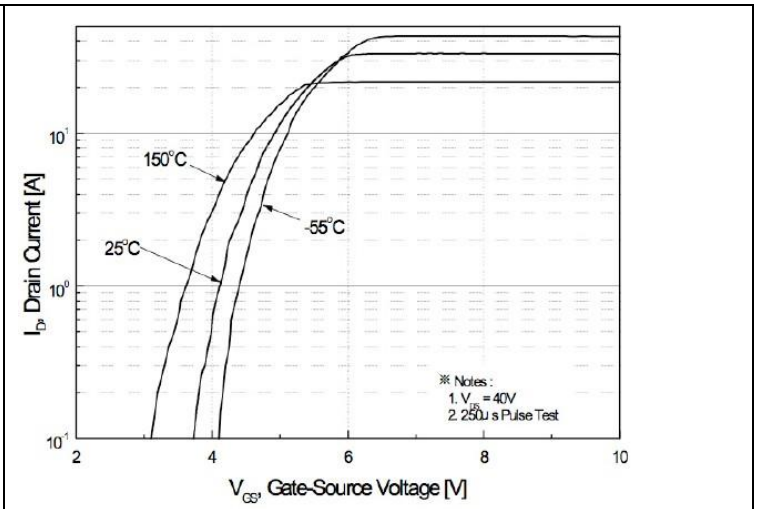


FIG. 2-TRANSFER CHARACTERISTICS

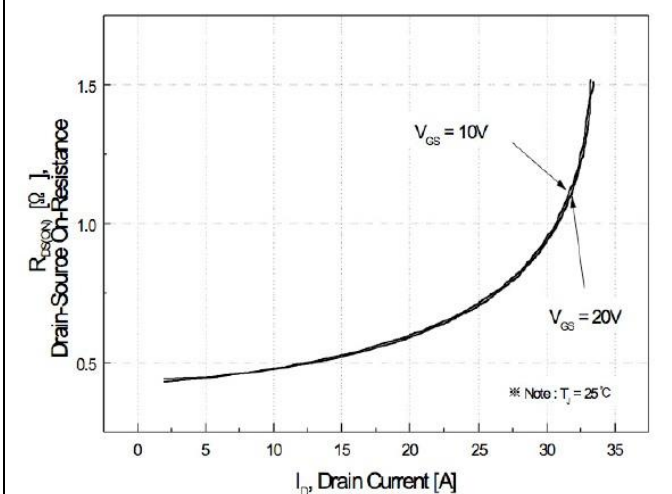


FIG. 3-ON RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

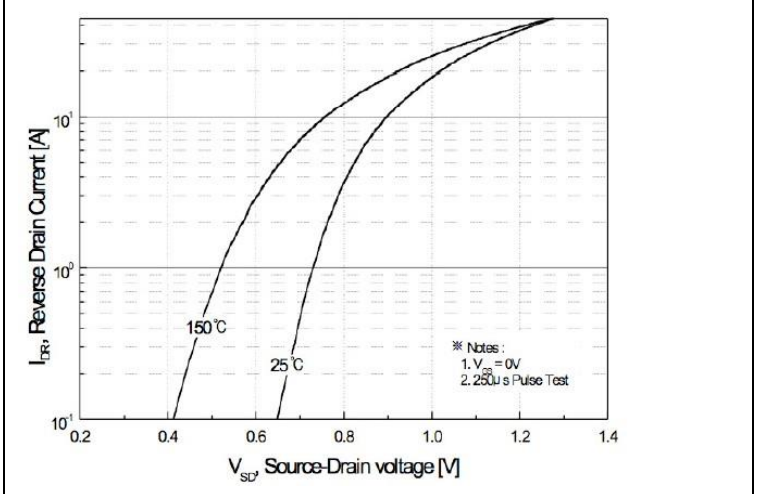


FIG. 4-BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

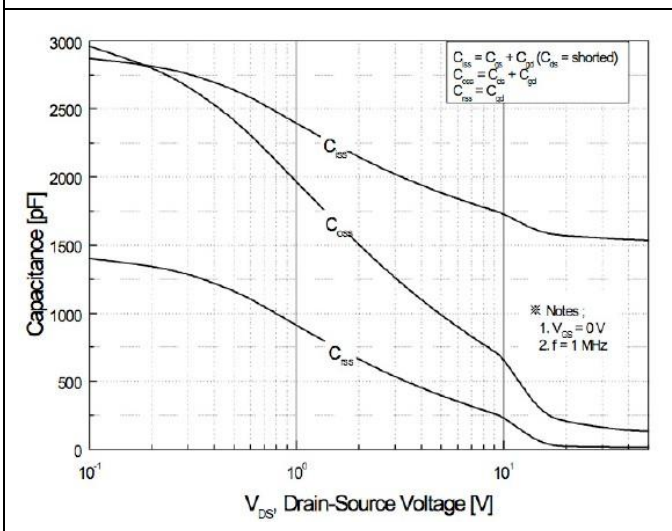


FIG. 5-CAPACITANCE CHARACTERISTICS

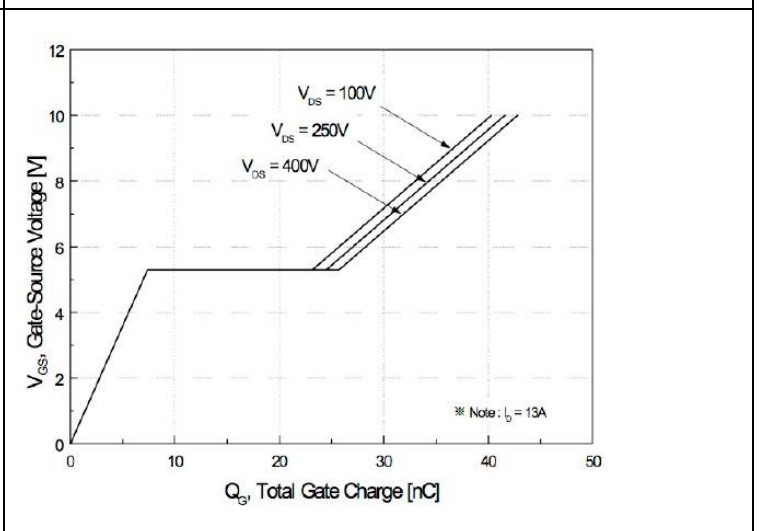


FIG. 6-GATE CHARGE CHARACTERISTICS

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#### ■ Characteristics Curve

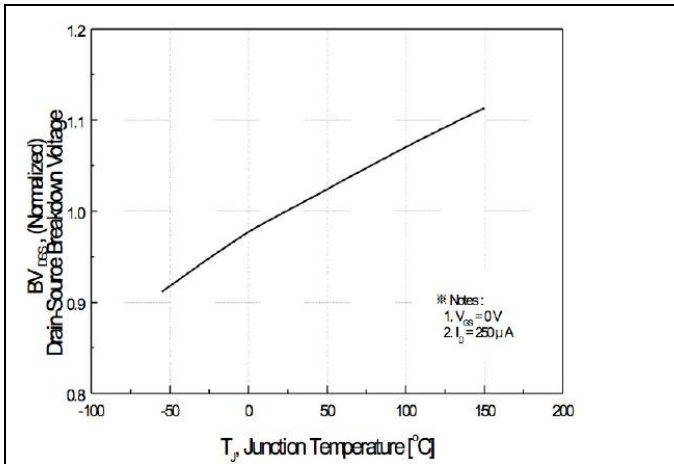


FIG. 7-BREAKDOWN VOLTAGE VARIATION VS TEMPERATURE

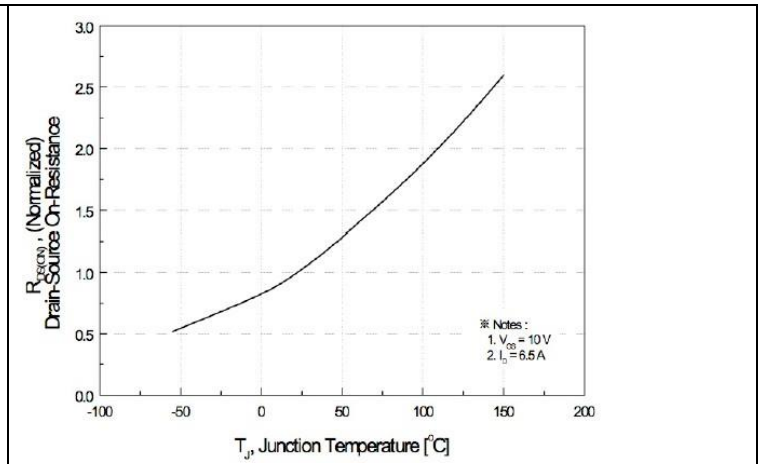


FIG. 8-ON-RESISTANCE VARIATION VS TEMPERATURE

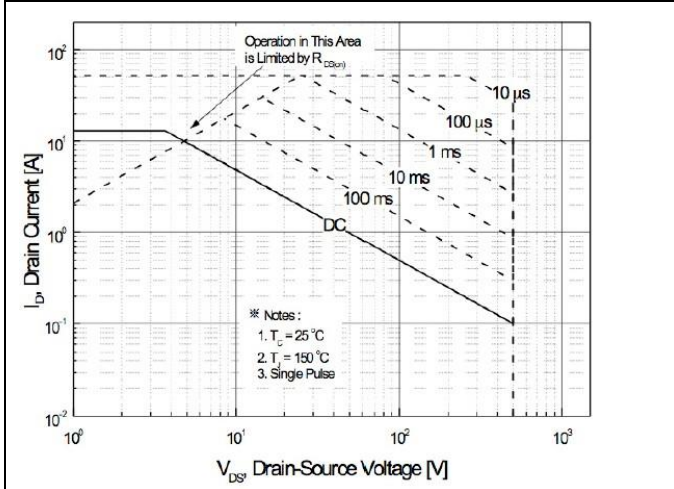


FIG. 9-MAXIMUM SAFE OPERATING AREA

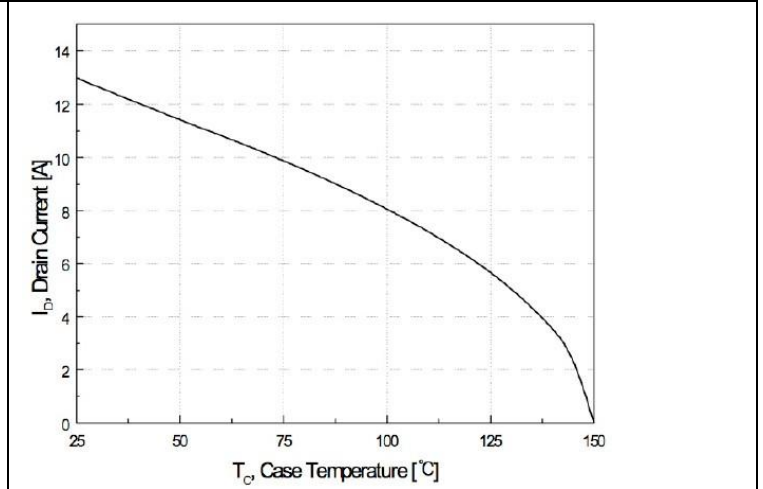


FIG. 10-MAXIMUM DRAIN CURRENT VS CASE TEMPERATURE

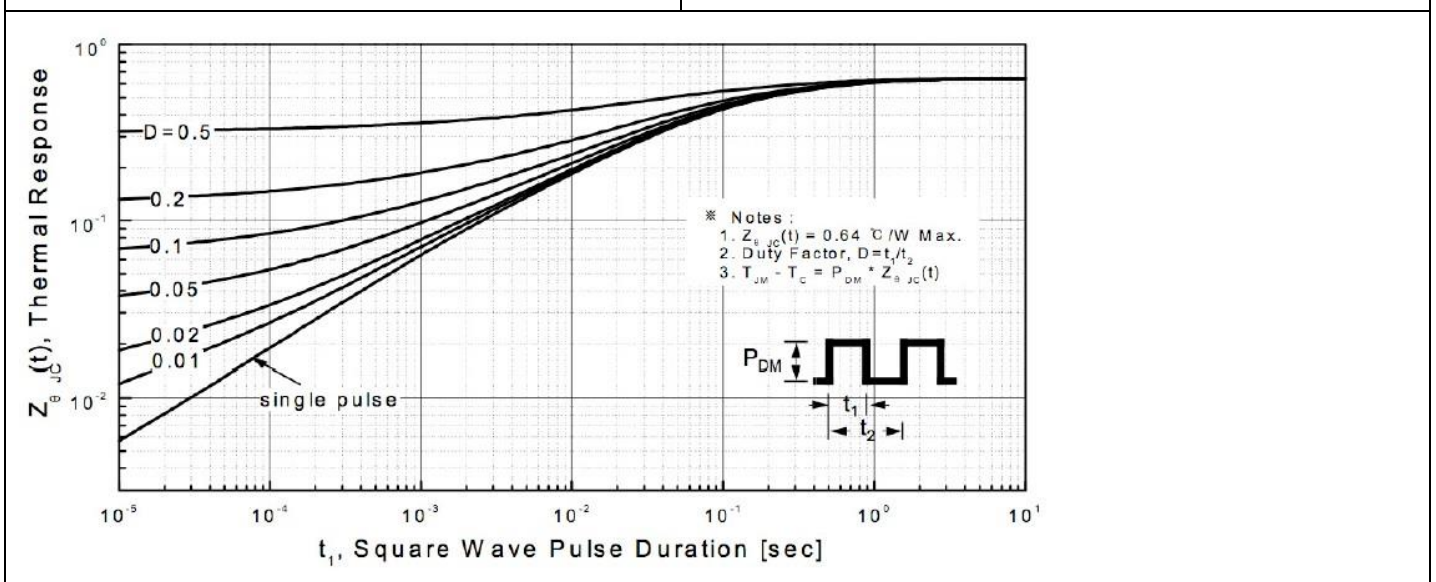


FIG. 11-TRANSIENT THERMAL RESPONSE CURVE

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#### Disclaimer

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